

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Wendell P. Noble Jr.	Examiner:	Unknown
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	303.412US4
Title:	VERTICAL GAIN CELL AND ARRAY FOR A DYNAMIC RANDOM ACCESS MEMORY AND METHOD FOR FORMING THE SAME		

INFORMATION DISCLOSURE STATEMENT

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicant's prior U.S. application, Serial No. 09/879602, filed on June 12, 2001, which is relied upon for an earlier filing date under 35 U.S.C. §120.

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

WENDELL P. NOBLE JR.

By his Representatives,

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Date Dec. 16, 2003

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Date of Deposit: December 16, 2003

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Noble Jr., Wendell
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 8

Attorney Docket No: 303.412US4

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First Named Inventor	Noble Jr., Wendell
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 2 of 8

Attorney Docket No: 303.412US4

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Substitute Disclosure Statement Form (PTO-1449)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>	<i>Complete if Known</i>	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Noble Jr., Wendell
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 3 of 8	Attorney Docket No: 303.412US4	

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
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EXAMINER

DATE CONSIDERED

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

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First Named Inventor	Noble Jr., Wendell
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 4 of 8

Attorney Docket No: 303.412US4

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EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1448)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td colspan="2" style="padding: 2px;"><i>Complete if Known</i></td> </tr> <tr> <td style="width: 60%; padding: 2px;">Application Number</td> <td style="padding: 2px;">Unknown</td> </tr> <tr> <td style="padding: 2px;">Filing Date</td> <td style="padding: 2px;">Even Date Herewith</td> </tr> <tr> <td style="padding: 2px;">First Named Inventor</td> <td style="padding: 2px;">Noble Jr., Wendell</td> </tr> <tr> <td style="padding: 2px;">Group Art Unit</td> <td style="padding: 2px;">Unknown</td> </tr> <tr> <td style="padding: 2px;">Examiner Name</td> <td style="padding: 2px;">Unknown</td> </tr> </table>	<i>Complete if Known</i>		Application Number	Unknown	Filing Date	Even Date Herewith	First Named Inventor	Noble Jr., Wendell	Group Art Unit	Unknown	Examiner Name	Unknown
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Examiner Name	Unknown

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Noble Jr., Wendell
	Group Art Unit	Unknown
	Examiner Name	Unknown
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	First Named Inventor	Noble Jr., Wendell
	Group Art Unit	Unknown
	Examiner Name	Unknown
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